

L Number	Hits	Search Text	DB	Time stamp
-	28	dram and (capacitor or capacitive or capacitance) near8 (aluminum adj nitride or aln or al adj n)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 09:40
-	13	(dram or sdram or memory) and (capacitor or capacitive or capacitance) near5 (dielectric or insulator or insulating) near5 (aluminum adj nitride or aln or al near2 n or al2n3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 15:34
-	23	(dram or sdram or memory) and (capacitor or capacitive or capacitance) near5 (dielectric or insulator or insulating) near5 (aluminum near3 nitride or aln or al near2 n or al2n3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 15:35
-	23	(dram or sdram or memory) and (capacitor or capacitive or capacitance) near5 (dielectric or insulator or insulating or spacer) near5 (aluminum near3 nitride or aln or al near2 n or al2n3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 15:39
-	15	("5183684" "5356608" "5573742" "5599732" "5605858" "5650361" "5656113" "5687112" "5709928" "5767578" "5773882" "5783483" "5783716" "5786259" "5786635").PN.	USPAT	2004/08/31 15:38
-	67	(capacitor or capacitive or capacitance or storage) near5 (dielectric or insulator or insulating or spacer) near5 (aluminum near3 nitride or aln or al near2 n or al2n3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 15:41
-	75	(capacitor or capacitive or capacitance or storage) near5 (dielectric or insulator or insulating or spacer) near5 (aluminum near3 nitride or aln or al near2 n or al2n3 or nitride near3 Al)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 16:21
-	64	(capacitor or capacitive or capacitance or storage) near5 (dielectric or insulator or insulating or spacer) near5 (metal near2 nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 16:22
-	898	257/310.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 08:50
-	110	257/310.ccls. and (aluminum near3 nitride or al near3 nitride or aln or al near2 n or "al2n3")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 08:51
-	111	257/310.ccls. and (aluminum near3 nitride or al near3 nitride or aln or al near2 n or "al2n3" or alno or alon or aluminum near3 oxynitride or nitrided near2 alumina)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 08:52
-	111	257/310.ccls. and (aluminum near3 nitride or al near3 nitride or aln or al near2 n or "al2n3" or alno or alon or aluminum near3 oxynitride or nitrided near2 alumina or nitride near alumina)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 09:40
-	14	("4455568" "5032892" "5079609" "5212402" "5266821" "5366931" "5656834" "5668399" "5932905" "5940676" "5955758" "5972791" "5973908" "6034391").PN.	USPAT	2004/09/01 09:11
-	1576	(dram or sdram or memory) and (insulator or insulating or dielectric) near6 ((aluminum or alumina or al) near4 (nitride or n or nitrided or oxynitride) or aln)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 09:42

-	320	(dram or sdram) and (insulator or insulating or dielectric) near5 ((aluminum or alumina or al) near3 (nitride or n or nitrided or oxynitride) or aln)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 09:43
-	36	(dram or sdram) and (insulator or insulating or dielectric) near5 ((aluminum or alumina or al) near3 (nitride or n or nitrided or oxynitride) or aln) near15 (capacitor or capacitive or capacitance)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 10:26
-	14	6218293.pn. 6294420.pn. 6307775.pn. 6358810.pn. 5183684.pn. 6372530.pn. 6072211.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 10:37
-	3	257/68.ccls. and (insulator or insulating or spacer or dielectric) near8 ((aluminum or alumina or al) near8 (nitride or nitrided or nitrate or n or oxynitride or oxinitride or oxy-nitride or nitridation or nitrdation) or aln or al2n3 or alon or alno or alxny)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 10:39
-	6	257/71.ccls. and (insulator or insulating or spacer or dielectric) near8 ((aluminum or alumina or al) near8 (nitride or nitrided or nitrate or n or oxynitride or oxinitride or oxy-nitride or nitridation or nitrdation) or aln or al2n3 or alon or alno or alxny)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 10:41
-	76	257/296.ccls. and (insulator or insulating or spacer or dielectric) near8 ((aluminum or alumina or al) near8 (nitride or nitrided or nitrate or n or oxynitride or oxinitride or oxy-nitride or nitridation or nitrdation) or aln or al2n3 or alon or alno or alxny)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 11:56
-	5	("4141022" "5998269" "6326657" "6531750" "6548871").PN.	USPAT	2004/09/01 11:05
-	10	257/298.ccls. and (insulator or insulating or spacer or dielectric) near8 ((aluminum or alumina or al) near8 (nitride or nitrided or nitrate or n or oxynitride or oxinitride or oxy-nitride or nitridation or nitrdation) or aln or al2n3 or alon or alno or alxny)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 11:58
-	13	257/300.ccls. and (insulator or insulating or spacer or dielectric) near8 ((aluminum or alumina or al) near8 (nitride or nitrided or nitrate or n or oxynitride or oxinitride or oxy-nitride or nitridation or nitrdation) or aln or al2n3 or alon or alno or alxny)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 12:08
-	15	5977582.URPN.	USPAT	2004/09/01 12:05
-	16	257/301.ccls. and (insulator or insulating or spacer or dielectric) near8 ((aluminum or alumina or al) near8 (nitride or nitrided or nitrate or n or oxynitride or oxinitride or oxy-nitride or nitridation or nitrdation) or aln or al2n3 or alon or alno or alxny)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 12:17
-	8	257/302.ccls. and (insulator or insulating or spacer or dielectric) near8 ((aluminum or alumina or al) near8 (nitride or nitrided or nitrate or n or oxynitride or oxinitride or oxy-nitride or nitridation or nitrdation) or aln or al2n3 or alon or alno or alxny)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 12:19
-	22	257/303.ccls. and (insulator or insulating or spacer or dielectric) near8 ((aluminum or alumina or al) near8 (nitride or nitrided or nitrate or n or oxynitride or oxinitride or oxy-nitride or nitridation or nitrdation) or aln or al2n3 or alon or alno or alxny)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 12:22
-	12	257/304.ccls. and (insulator or insulating or spacer or dielectric) near8 ((aluminum or alumina or al) near8 (nitride or nitrided or nitrate or n or oxynitride or oxinitride or oxy-nitride or nitridation or nitrdation) or aln or al2n3 or alon or alno or alxny)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 12:46

-	6	257/305.ccls. and (insulator or insulating or spacer or dielectric) near8 ((aluminum or alumina or al) near8 (nitride or nitrided or nitrate or n or oxynitride or oxinitride or oxy-nitride or nitridation or nitrdation) or aln or al2n3 or alon or alno or alxny)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 12:47
-	66	257/306.ccls. and (insulator or insulating or spacer or dielectric) near8 ((aluminum or alumina or al) near8 (nitride or nitrided or nitrate or n or oxynitride or oxinitride or oxy-nitride or nitridation or nitrdation) or aln or al2n3 or alon or alno or alxny)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 13:05
-	8	257/311.ccls. and (insulator or insulating or spacer or dielectric) near8 ((aluminum or alumina or al) near8 (nitride or nitrided or nitrate or n or oxynitride or oxinitride or oxy-nitride or nitridation or nitrdation) or aln or al2n3 or alon or alno or alxny)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 13:08
-	50	257/532.ccls. and (insulator or insulating or spacer or dielectric) near8 ((aluminum or alumina or al) near8 (nitride or nitrided or nitrate or n or oxynitride or oxinitride or oxy-nitride or nitridation or nitrdation) or aln or al2n3 or alon or alno or alxny)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 13:10
-	120	memory near8 (capacitor or capacitance) and (capacitor or capacitance or capacitive) near8 (dielectric or insulator or insulating or spacer or insulative) near8 (alumina or aluminum near2 oxide or al near2 o or alo or aluminum near nitride or al near2 n or aln)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 10:18
-	15	("5183684" "5356608" "5573742" "5599732" "5605858" "5650361" "5656113" "5687112" "5709928" "5767578" "5773882" "5783483" "5783716" "5786259" "5786635").PN.	USPAT	2004/09/07 09:59
-	61	memory near8 (capacitor or capacitance) and (capacitor or capacitance or capacitive) near8 (dielectric or insulator or insulating or spacer or insulative) near8 (metal near2 nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 14:14
-	4	("4058430" "4861417" "5166092" "5256244").PN.	USPAT	2004/09/07 10:30
-	81	(capacitor or capacitance) near3 (dielectric or insulator or diel or insulating or insulative or ins or spacer or gap) near10 (aluminum near3 nitride or aln or al near2 n)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 15:13
-	8	("5525542" "5578523" "5652176" "5674771" "5734177" "5812364" "6255187" "6329234").PN.	USPAT	2004/09/07 14:25
-	1	"5789320".PN.	USPAT	2004/09/07 14:32
-	29	US-5656113-\$.DID. OR US-5709928-\$.DID. OR US-5605858-\$.DID. OR US-5687112-\$.DID. OR US-5767578-\$.DID. OR US-5773882-\$.DID. OR US-5783483-\$.DID. OR US-5783716-\$.DID. OR US-5786635-\$.DID. OR US-5786259-\$.DID. OR US-5183684-\$.DID. OR US-5356608-\$.DID. OR US-5573742-\$.DID. OR US-5599732-\$.DID. OR US-5650361-\$.DID.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 15:15
-	4	6294420.pn. 6307775.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 15:23
-	2	6358810.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 15:37

-	6	6181056.pn. 6218771.pn. 6459096.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/07 15:40
-	2	6072211.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/07 15:43
-	2	6218293.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/07 15:43